





**SN74AVC1T45** 

SCES530J - DECEMBER 2003 - REVISED AUGUST 2024

# SN74AVC1T45 Single-Bit Dual-Supply Bus Transceiver With Configurable Voltage **Translation and 3-State Outputs**

### 1 Features

Texas

INSTRUMENTS

- Available in the Texas Instruments NanoFree<sup>™</sup> package
- Fully configurable dual-rail design allows each port to operate over the full 1.08V to 3.6V power-supply range
- V<sub>CC</sub> isolation feature if either V<sub>CC</sub> input is at GND, then both ports are in the high-impedance state
- DIR input circuit referenced to V<sub>CCA</sub>
- ±12mA output drive at 3.3V
- I/Os are 4.6V tolerant
- Ioff supports partial-power-down mode operation
- Typical maximum data rates
  - 500Mbps (1.08V to 3.3V translation)
  - 320Mbps (<1.8V to 3.3V translation) \_
  - 320Mbps (translate to 2.5V or 1.8V)
  - 280Mbps (translate to 1.5V)
  - 240Mbps (translate to 1.2V)
- Latch-up performance exceeds 100mA per JESD 78, Class II
- ESD protection exceeds JESD 22
  - ±2000V Human Body Model (A114-A)
  - 200V Machine Model (A115-A)
  - ±1000V Charged-Device Model (C101)

### 2 Applications

- Personal electronic
- Industrial
- Enterprise
- Telecom

### **3 Description**

This single-bit noninverting bus transceiver uses two separate configurable power-supply rails. The SN74AVC1T45 is operational with  $V_{CCA}/V_{CCB}$  as low as 1.08V.

The A port is designed to track V<sub>CCA</sub>. V<sub>CCA</sub> accepts any supply voltage from 1.08V to 3.6V. The B port is designed to track V<sub>CCB</sub>. V<sub>CCB</sub> accepts any supply voltage from 1.08V to 3.6V. This allows for universal low-voltage, bidirectional translation between any of the 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V voltage nodes.

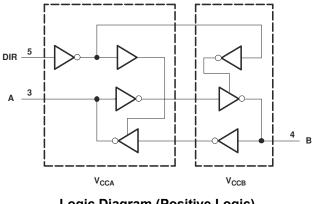
The SN74AVC1T45 is designed for asynchronous communication between two data buses. The logic levels of the direction-control (DIR) input activate either the B-port outputs or the A-port outputs. The device transmits data from the A bus to the B bus when the B-port outputs are activated and from the B bus to the A bus when the A-port outputs are activated. The input circuitry on both A and B ports always is active and must have a logic HIGH or LOW level applied to prevent excess  $I_{CC}$  and  $I_{CCZ}$ .

The SN74AVC1T45 is designed so that the DIR input is powered by  $V_{CCA}$ .

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The V<sub>CC</sub> isolation feature is designed so that if either V<sub>CC</sub> input is at GND, then both ports are in the highimpedance state.

technology NanoFree package major is а breakthrough in IC packaging concepts, using the die as the package.



Logic Diagram (Positive Logic)



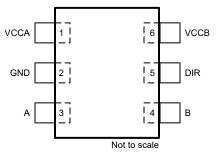
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### **4** Pin Configuration and Functions



### Figure 4-1. DCK Package, 6-Pin SOT-SC70 (Top View)

See mechanical drawings in *Section 11* for dimensions.

#### Table 4-1. Pin Functions

	PIN	TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		DESCRIPTION
V <sub>CCA</sub>	1	Р	A-port supply voltage. $1.08V \le V_{CCA} \le 3.6V$
GND	2	G	Ground
A	A 3 I/O Input/output A. Refere		Input/output A. Referenced to V <sub>CCA</sub> .
В	4	I/O	Input/output B. Referenced to V <sub>CCB</sub> .
DIR	5	I	Direction control signal
V <sub>CCB</sub>	6	Р	B-port supply voltage. $1.08V \le V_{CCB} \le 3.6V$ .

(1) I =input, O = output, P = power, G = ground

### **5** Specifications

#### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	TYP	MAX	UNIT
V <sub>CCB</sub>	Supply voltage B		-0.5	2	5.5	V
		I/O Ports (A Port)	-0.5		4.6	
VI	Input Voltage <sup>(2)</sup>	I/O Ports (B Port)	-0.5		4.6	V
		Control Inputs	-0.5	2	4.6	
V	Voltage applied to any output in the high-impedance or	A Port	-0.5		4.6	v
Vo	power-off state <sup>(2)</sup>	B Port	-0.5		4.6	
V	) (altern applied to any autout in the high or law state(2) (3)	A Port	-0.5		V <sub>CCA</sub> + 0.5	v
Vo	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	B Port	-0.5		V <sub>CCB</sub> + 0.5	
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0	-50			mA
I <sub>OK</sub>	Output clamp current	V <sub>0</sub> < 0	-50			mA
lo	Continuous output current	·	-50		50	mA
	Continuous current through V <sub>CC</sub> or GND		-100		100	mA
Tj	Junction Temperature				150	°C
T <sub>stg</sub>	Storage temperature		-65		150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Section 5.2 Exposure beyond the limits listed in Section 5.2 may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

### **5.2 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

				MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage A			1.08	3.6	v
V <sub>CCB</sub>	Supply voltage B			1.08	3.6	v
			V <sub>CCI</sub> = 1.08V	V <sub>CCI</sub> x 0.7		
V	High-level input	Data inputs	V <sub>CCI</sub> = 1.1V to 1.95V	V <sub>CCI</sub> x 0.65		v
VIH	voltage	Data inputs	V <sub>CCI</sub> = 2V to 2.7V	1.6		
			V <sub>CCI</sub> = 2.8V to 3.6V	2		
			V <sub>CCI</sub> = 1.08V		V <sub>CCI</sub> x 0.3	
V	Low-level input	Data innuta	V <sub>CCI</sub> = 1.1V to 1.95V		V <sub>CCI</sub> x 0.35	v
VIL	voltage	Data inputs	V <sub>CCI</sub> = 2V to 2.7V		0.7	
			V <sub>CCI</sub> = 2.8V to 3.6V		0.8	
			V <sub>CCA</sub> = 1.08V to 1.95V	V <sub>CCA</sub> x 0.65		
VIH	High-level input voltage	Control inputs (refrenced to $V_{CCA}$ )	V <sub>CCA</sub> = 2V to 2.7V	1.7		V
	linage		V <sub>CCA</sub> = 2.8V to 3.6V	2		
			V <sub>CCA</sub> = 1.08V to 1.95V		V <sub>CCA</sub> x 0.35	
V.,	Low-level input voltage	Control inputs (refrenced to V <sub>CCA</sub> )	V <sub>CCA</sub> = 2V to 2.7V		0.7	V
	Voltage V <sub>CCA</sub>		V <sub>CCA</sub> = 2.8V to 3.6V		0.8	



over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

				MIN	MAX	UNIT
			V <sub>CCO</sub> = 1.08V to 1.32V		-3	
			V <sub>CCO</sub> = 1.4V to 1.6V		-6	
I <sub>OH</sub>	High-level output o	current	V <sub>CCO</sub> = 1.65V to 1.95V		-8	mA
			V <sub>CCO</sub> = 2.3V to 2.7V		-9	
			V <sub>CCO</sub> = 3V to 3.6V		-12	
			V <sub>CCO</sub> = 1.08V to 1.32V		3	
			V <sub>CCO</sub> = 1.4V to 1.6V		6	
I <sub>OL</sub>	Low-level output c	urrent	V <sub>CCO</sub> = 1.65V to 1.95V		8	mA
			V <sub>CCO</sub> = 2.3V to 2.7V		9	
			V <sub>CCO</sub> = 3V to 3.6V		12	
VI	Input voltage <sup>(3)</sup>			0	3.6	V
V	Output voltage	Active State		0	V <sub>CCO</sub>	V
Vo		Tri-State		0	3.6	v
Δt/Δv	Input transition rise	e and fall time	V <sub>CCI</sub> = 1.08V to 3.6V		5	ns/V
T <sub>A</sub>	Operating free-air	temperature		-40	125	°C

(1)

(2) (3)

 $V_{CCI}$  is the  $V_{CC}$  associated with the input port.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the II specification indicated under Section 5.4



#### **5.3 Thermal Information**

		SN74AV0	C1T45-Q1	
	THERMAL METRIC <sup>(1)</sup>	DCK (TSC70)	DRY (USON)	UNIT
		6 PINS	6 PINS	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	239.9	291.9	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	175.0	137.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	94.4	176.5	°C/W
Y <sub>JT</sub>	Junction-to-top characterization parameter	75.6	47.3	°C/W
Y <sub>JB</sub>	Junction-to-board characterization parameter	93.9	175.9	°C/W
R <sub>0JC(bottom)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



### **5.4 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

						0	perati	ng free	air tem	perat	ture (T⊿	)		
PA	RAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>		25°C		<b>-40</b> °	C to 85	°C	-40°0	C to 12	25°C	UNI
		CONDITIONS			MIN	TYP	MAX	MIN	TYP I	MAX	MIN	TYP	MAX	1
		I <sub>OH</sub> = –100 μA	1.08 V - 3.6 V	1.08 V - 3.6 V	VCC 0 - 0.2			V <sub>CCO</sub> - 0.2			V <sub>CCO</sub> - 0.2			
	High-level	I <sub>OH</sub> = –3 mA	1.1 V	1.1 V	0.85			0.85			0.85			]
V <sub>OH</sub>	output voltage <sup>(3)</sup>	I <sub>OH</sub> = –6 mA	1.4 V	1.4 V	1.05			1.05			1.05			V
	voltage	I <sub>OH</sub> = –8 mA	1.65 V	1.65 V	1.2			1.2			1.2			1
		I <sub>OH</sub> = –9 mA	2.3 V	2.3 V	1.75			1.75			1.75			1
		I <sub>OH</sub> = -12 mA	3 V	3 V	2.3			2.3			2.3			1
		I <sub>OL</sub> = 100 μA	1.08 V - 3.6 V	1.08 V - 3.6 V			0.1			0.15			0.15	
		I <sub>OL</sub> = 3 mA	1.1 V	1.1 V			0.2			0.22			0.22	1
	Low-level	I <sub>OL</sub> = 6 mA	1.4 V	1.4 V			0.28			0.30			0.31	v
V <sub>OL</sub>	output voltage <sup>(4)</sup>	I <sub>OL</sub> = 8 mA	1.65 V	1.65 V			0.32			0.35			0.35	V
		I <sub>OL</sub> = 9 mA	2.3 V	2.3 V			0.31			0.32			0.33	1
		I <sub>OL</sub> = 12 mA	3 V	3 V			0.40			0.40			0.40	1
I <sub>I</sub>	Input leakage	Control inputs (DIR, $\overline{OE}$ ) V <sub>I</sub> = V <sub>CCA</sub> or GND	1.08 V - 3.6 V	1.08 V - 3.6 V	-0.25		0.25	-1		1	-1		1	μA
	current	Data Inputs (Ax, Bx) V <sub>I</sub> = V <sub>CCI</sub> or GND	1.08 V - 3.6 V	1.08 V - 3.6 V	-0.25		0.25	-1		1	-1		1	μA
	Partial power	A Port or B Port	0 V	0 V - 3.6 V	-1	0.1	1	-2		2	-5		5	
l <sub>off</sub>	down current	V <sub>I</sub> or V <sub>O</sub> = 0 V - 3.6 V	0 V - 3.6 V	0 V	-1	0.1	1	-2		2	-5		5	μA
I <sub>OZ</sub>	Tri-state output current <sup>(5)</sup>	A or B Port: $V_1 = V_{CCI}$ or GND $V_0 = V_{CCO}$ or GND $\overline{OE} = V_{IH}$	3.6 V	3.6 V	-0.5	0.5	0.5	-1		1	-1		1	μA
			1.08 V - 3.6 V	1.08 V - 3.6 V			2			2.5			4	
I <sub>CCA</sub>	V <sub>CCA</sub> supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	0 V	3.6 V	-0.2			-2			-2			μA
	ounone		3.6 V	0 V			1			2			2.5	1
			1.08 V - 3.6 V	1.08 V - 3.6 V			2.5			3.5			5	
I <sub>CCB</sub>	V <sub>CCB</sub> supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	0 V	3.6 V			1			2			3	μA
	ounone		3.6 V	0 V	-0.2			-2			-2			
I <sub>CCA</sub> + I <sub>CCB</sub>	Combined supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	1.08 V - 3.6 V	1.08 V - 3.6 V			3			5			8	μA
C <sub>i</sub>	Control Input Capacitance	V <sub>I</sub> = 3.3 V or GND	3.3 V	3.3 V		2.5				2.5			2.5	pF
C <sub>io</sub>	Data I/O Capacitance	$\overline{OE} = V_{CCA}, V_O = 1.65V DC + 1$ MHz -16 dBm sine wave	3.3 V	3.3 V		6				4			6	pF

 $V_{CCI}$  is the  $V_{CC}$  associated with the input port.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. Tested at  $V_I = V_{T+(MAX)}$ . (1) (2)

(3)

Tested at V<sub>I</sub> = V<sub>T-(MIN)</sub>. (4)



(5) For I/O ports, the parameter  $I_{\text{OZ}}$  includes the input leakage current.



### 5.5 Switching Characteristics, $V_{CCA} = 1.2 \pm 0.12 V$

										B-P	ort Sup	ply Vol	tage (V <sub>c</sub>	:св)												
	PARAMETER	FROM	то	TEST CONDITIONS	1.2	2 ± 0.12	V	1.	5 ± 0.1	v	1.8	3 ± 0.15	V	2.	5 ± 0.2	v	3.	3 ± 0.3	v	UNIT						
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX							
		A	В	-40°C to 85°C	3.0	3.1	10.8	2.3	2.6	7.7	2.1	2.5	6.6	1.9	3	5.3	1.8	3.5	5							
+ .	Propagation delay		В	-40°C to 125°C	3.1	3.1	10.2	2.6	2.6	7.4	2.3	2.5	6.5	2.1	3	5.4	1.9	3.5	5.1	ne						
t <sub>pd</sub>	Fiopagation delay	в	A	-40°C to 85°C	2.9	3.1	10.6	2.0	2.7	7.6	1.8	2.5	6.5	1.8	2.4	5.2	1.8	2.3	4.8	ns						
	B A		-40°C to 125°C	3.1	3.1	10.2	2.3	2.7	7.8	2.1	2.5	6.7	2.0	2.4	5.4	2.0	2.3	5.0								
		OE A	^	-40°C to 85°C	3.3	5.3	12	3.3	5.3	12	3.5	5.3	12	3.5	5.3	12	3.5	5.3	12							
	Enable time	UE	A	-40°C to 125°C	3.8	5.3	12.8	3.8	5.3	12.8	3.8	5.3	12.7	3.8	5.3	12.7	3.7	5.3	12.3							
t <sub>en</sub>			в	-40°C to 85°C	3	5.1	12	3	4	7.5	2.5	3.5	5.9	2	3.2	4.7	2	3.1	4.7	ns						
		ŌĒ	ŌĒ	ŌE	ŌĒ	ŌĒ	ŌĒ	Б	-40°C to 125°C	3.5	5.1	12	2.8	4	7.4	2.5	3.5	6	2.1	3.2	4.9	2.1	3.1	4.7		
							OF		•	-40°C to 85°C	5.0	4.8	8.5	5.0	4.8	8.5	5.0	4.8	8.3	5.0	4.8	8.5	5.0	4.8	8.5	
		OE A	OE A	OE A	OE /	ŌĒ	OE	OE .	OE /	-40°C to 125°C	4.9	4.8	9.2	4.9	4.8	9.2	4.9	4.8	9.2	4.9	4.8	9.2	4.9	4.8	9.2	
t <sub>dis</sub>		Disable time				Б	-40°C to 85°C	5.6	4.7	11.4	4.8	4	9.3	5.2	4.1	9.1	4.0	4.3	7.1	5.0	5.1	8.3	ns			
		D	-40°C to 125°C	5.6	4.7	11.6	4.8	4	9.4	5.2	4.1	9.3	4.0	7.6	7.3	5.0	5.1	8.4								

### 5.6 Switching Characteristics, $V_{CCA} = 1.5 \pm 0.1 V$

										B-P	ort Sup	ply Volt	age (V <sub>C</sub>	:св)										
	PARAMETER	FROM	то	TEST CONDITIONS	1.:	2 ± 0.12	V	1.	5 ± 0.1	v	1.8	3 ± 0.15	V	2.	5 ± 0.2	V	3.	3 ± 0.3	v	UNIT				
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX					
			В	-40°C to 85°C	2.0	2.7	7.2	1.7		5.3	1.5		4.5	1.2		3.9	1.1		3.4					
+ .	Propagation delay	A	В	-40°C to 125°C	2.3	2.7	7.3	1.9		5.3	1.8		4.5	1.5		3.9	1.3		3.4	ns				
Lpd	Fiopagation delay	в	^	-40°C to 85°C	1.6	2.3	7.1	1.7		5.2	1.5		5.1	1.4		4.6	1.4		4.4	115				
		D	A	-40°C to 125°C	1.8	2.3	7.0	1.9		5.2	1.8		5.1	1.6		4.6	1.5		4.4					
		ŌĒ	^	-40°C to 85°C	3.0	3.7	7.0	2.9		7.6	2.8		6.9	2.7		7.5	2.6		6.6					
+	Enable time	UE	A	-40°C to 125°C	3.0	3.8	7.2	2.9		7.6	2.8		7.6	2.7		7.5	2.6		7.3	ns				
l'en				Enable time		OE	в	-40°C to 85°C	3.4	4.8	11.2	2.7		7.6	2.3		5.6	1.9		4.4	1.8		5.3	115
				-40°C to 125°C	3.4	5.1	11.2	2.7		7.7	2.3		5.6	1.9		4.4	1.8		4.5					



## 5.6 Switching Characteristics, $V_{CCA}$ = 1.5 ± 0.1 V (continued)

										B-Pe	ort Sup	ply Volt	tage (V <sub>C</sub>	св)																	
	PARAMETER	FROM	то	TEST CONDITIONS	1.2	2 ± 0.12	V	1.	.5 ± 0.1 \	/	1.8	3 ± 0.15	۷	2.	5 ± 0.2	v	3.	3 ± 0.3 \	V	UNIT											
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX												
			^	-40°C to 85°C	4.1	3.1		4.1		8.6	4.0		9.6	4.0		9	4.0		8.7												
+	Disable time	ŌĒ	JF	ЭЕ	OE	OE	OE	JE	^	-40°C to 125°C	4.1	4.8		3.2		8.6	4.0		9.6	4.0		9	4.0		8.6	ns					
<sup>t</sup> dis															-40°C to 85°C	5.3	4.1	10	4.5		8.4	4.9		8.5	3.7		7.2	4.8		7.8	115
			D	-40°C to 125°C	5.3	4.7	9.9	4.5		8.4	4.9		8.7	3.7		7.2	4.8		7.8												

### 5.7 Switching Characteristics, $V_{CCA}$ = 1.8 ± 0.15 V

										B-P	ort Sup	ply Volt	tage (V <sub>C</sub>	:св)												
	PARAMETER	FROM	то	TEST CONDITIONS	1.2	2 ± 0.12	V	1.	.5 ± 0.1 \	/	1.8	8 ± 0.15	V	2.	5 ± 0.2	v	3.	3 ± 0.3 \	v	UNIT						
					MIN	TYP	MAX	MIN	ΤΥΡ	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX							
		A	В	-40°C to 85°C	1.9	2.5	6.2	1.5		5.1	1.4		4.4	1.1		4	1.0		3.9							
	Propagation dolor	<b>^</b>	Б	-40°C to 125°C	2.1	2.5	6.3	1.8		5.1	1.7		4.4	1.3		4	1.2		3.9	ns						
t <sub>pd</sub>	Propagation delay	В	A	-40°C to 85°C	2.1	2.5	6.5	1.5		4.6	1.4		4.4	1.3		3.9	1.1		3.7	115						
		Б		-40°C to 125°C	2.3	2.5	6.3	1.8		4.6	1.7		4.4	1.5		3.9	1.4		3.7							
		OE	^	-40°C to 85°C	2.4	3	5.4	2.4		6.8	2.4		6.8	2.3		6.8	2.2		6.8							
	Enable time		A	-40°C to 125°C	2.4	3	5.4	2.4		6.8	2.4		6.8	2.3		6.8	2.2		6.8	20						
t <sub>en</sub>		ŌE	В	-40°C to 85°C	3.3	4.6	11.0	2.5		8.2	2.1		6.7	1.7		5.1	1.6		4.5	ns						
		UE	P	-40°C to 125°C	3.3	4.6	11.0	2.5		8.2	2.1		6.7	1.7		5.1	1.6		4.5							
		OF	^	-40°C to 85°C	4.4	2.7		4.3		7.1	4.3		7.1	4.3		7.1	4.2		7.1							
		OE A	-40°C to 125°C	4.4	2.7		4.3		7.1	4.3		7.1	4.3		7.1	4.2		7.1	<b>n</b> 0							
t <sub>dis</sub>									Р	-40°C to 85°C	5.1	3.9	9	4.3		7.8	4.7		8.1	3.6		6	4.6		7.2	ns
			D	-40°C to 125°C	5.1	3.9	9	4.3		7.8	4.7		8.3	3.6		6	4.6		7.4							



### 5.8 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2 V$

	PARAMETER		то		B-Port Supply Voltage (V <sub>CCB</sub> )															
				TEST CONDITIONS	1.2 ± 0.12 V			1.5 ± 0.1 V		1.8 ± 0.15 V		2.5 ± 0.2 V			3.	3 ± 0.3 \	V	UNIT		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
		A	В	-40°C to 85°C	1.8	2.4	5	1.4		4.7	1.3		3.9	1.1		3.1	0.9		2.8	
	Propagation delay		В	-40°C to 125°C	2.0	2.4	5.1	1.6		4.7	1.5		3.9	1.3		3.1	1.0		2.8	ns
t <sub>pd</sub>	Fiopagation delay	в	A	-40°C to 85°C	1.9	2.2	5.5	1.3		4.2	1.1		3.8	1.1		3.1	1		2.9	115
				-40°C to 125°C	2.1	2.2	5.2	1.5		4.2	1.3		3.8	1.3		3.1	1.1		2.9	
	Enable time	ŌĒ	A	-40°C to 85°C	1.9	2.2	3.8	1.9		3.8	1.9		3.8	1.9		3.8	1.9		3.8	
				-40°C to 125°C	1.9	2.2	3.8	1.9		3.8	1.9		3.8	1.9		3.8	1.9		3.8	ns
t <sub>en</sub>		ŌE	В	-40°C to 85°C	2.9	4.5	10.8	2.2		7.6	1.8		6.5	1.5		4.1	1.3		4	
			В	-40°C to 125°C	2.9	4.5	10.8	2.2		7.6	1.8		6.5	1.5		4.1	1.3		4	
		ŌĒ	^	-40°C to 85°C	3.0	1.8	5.5	3.0		5.1	3.0		5.1	3.0		5.1	2.9		5.1	
	Dischle time	UE	A	-40°C to 125°C	2.7	1.8	5.5	2.7		5.1	2.6		5.1	2.9		5.1	2.7		5.1	
t <sub>dis</sub>	Disable time	ŌĒ	в	-40°C to 85°C	5.0	3.6	9	4.2		7.1	4.6		7.3	3.5		5.7	4.6		6.8	ns
			D	-40°C to 125°C	5.0	3.6	9	4.2		7.1	4.6		7.5	3.2		5.8	4.2		7.0	

### 5.9 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3 V$

					B-Port Supply Voltage (V <sub>CCB</sub> )																
	PARAMETER		то	TEST CONDITIONS	1.2 ± 0.12 V		1.5 ± 0.1 V		v	1.8 ± 0.15 V		2.5 ± 0.2 V		V	3.3 ± 0.3 V		v	UNIT			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
		^	в	-40°C to 85°C	1.8	2.3	4.8	1.4		4.5	1.2		3.3	1.1		2.9	0.9		2.5		
t <sub>pd</sub>	Propagation delay	A	В	-40°C to 125°C	2.0	2.3	5.2	1.5		4.5	1.4		3.3	1.1		2.9	1.0		2.5	ns	
		В	A	-40°C to 85°C	1.8	2.2	5.2	1.2		3.8	1.0		3.4	0.9		2.8	0.9		2.5	115	
				-40°C to 125°C	1.9	2.2	5	1.3		3.8	1.2		3.4	1.1		2.8	1.0		2.5		
		ŌĒ	^	-40°C to 85°C	1.8	2	3	1.8		4	1.8		4	1.8		4	1.8		4		
t <sub>en</sub>	Enable time	UE	A	-40°C to 125°C	1.8	2	3.2	1.8		4	1.8		4	1.8		4	1.8		4	20	
		ŌE		В	-40°C to 85°C	2.7	4	10	1.9		7.4	1.6		6.2	1.3		4	1.2		3.9	ns
		OE		-40°C to 125°C	2.7	4	10	1.9		7.4	1.6		6.2	1.3		4	1.2		3.9		



## 5.9 Switching Characteristics, $V_{CCA}$ = 3.3 $\pm$ 0.3 V (continued)

			то	TEST	B-Port Supply Voltage (V <sub>CCB</sub> )															
	PARAMETER	FROM			1.2 ± 0.12 V		1.5 ± 0.1 V		1.8 ± 0.15 V		۷	2.5 ± 0.2 V		V	3.3 ± 0.3 V		v	UNIT		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>dis</sub>	Disable time	ŌE	^	-40°C to 85°C	4.0	5	6	3.9		5.9	3.9		5.9	3.9		5.9	3.9		5.8	
				-40°C to 125°C	4.0	5	6	3.9		6.0	3.9		6.0	3.9		6.0	3.9		6.0	ns
		ŌE	в	-40°C to 85°C	5.0	6	8	4.2		6.9	4.7		7.1	3.7		5.5	4.6		6.6	115
				-40°C to 125°C	5.0	6	8	4.2		6.9	4.1		7.3	3.2		5.5	4.2		6.8	



### **5.10 Operating Characteristics**

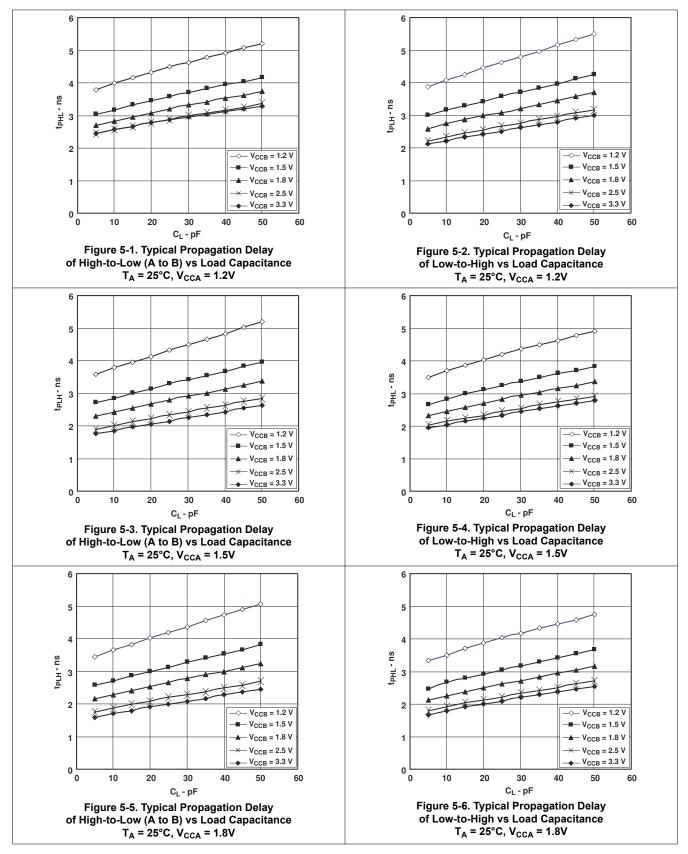
T<sub>A</sub> = 25°C <sup>(1)</sup>

			Si	upply Voltage	$(V_{CCB} = V_{CCA})$		
	PARAMETER	Test Conditions	1.2 ± 0.12V	1.8 ± 0.15V	2.5 ± 0.2V	3.3 ± 0.3V	UNIT
			TYP	TYP	TYP	TYP	
	A to B: outputs enabled		3	3	3	4	
C <sub>pdA</sub> <sup>(2)</sup>	A to B: outputs disabled		3	3	3	4	
⊂pdA	B to A: outputs enabled	A Port	13	13	15	15	
	B to A: outputs disabled	CL = 0, RL = Open	3	3	3	4	рF
	A to B: outputs enabled	f = 10 MHz	13 13	15	15	рг	
C (2)	A to B: outputs disabled	t <sub>rise</sub> = t <sub>fall</sub> = 1 ns	$l_{rise} - l_{fall} - 1 fis$ 3	3	3	3	
C <sub>pdB</sub> <sup>(2)</sup>	B to A: outputs enabled		3	3	3	3	
	B to A: outputs disabled		3	3	3	3	

For more information about power dissipation capacitance, see the CMOS Power Consumption and C<sub>pd</sub> Calculation application report.
 C<sub>pdA</sub> and C<sub>pdB</sub> are repectively A-Port and B-Port power dissipation capacitances per transceiver.

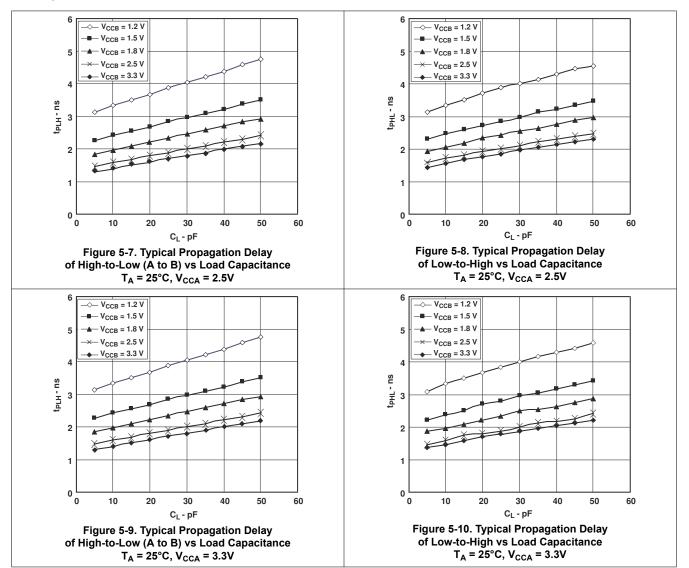


### **5.11 Typical Characteristics**

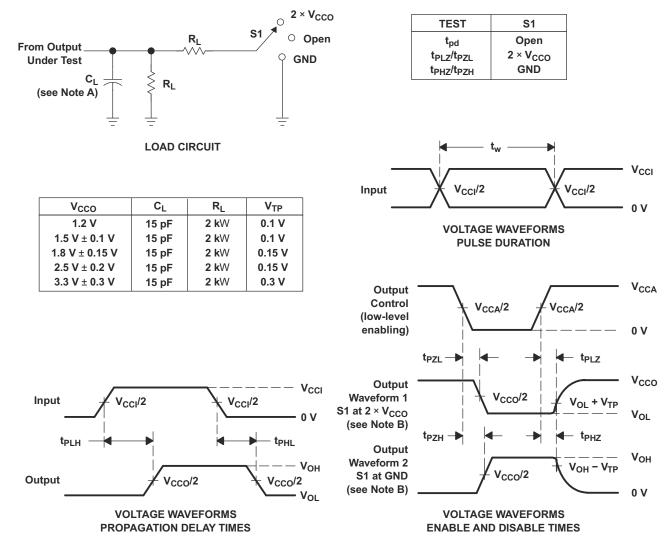




#### 5.11 Typical Characteristics (continued)







- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz,  $Z_0 = 50$  W dv/dt  $\ge 1$  V/ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H.  $V_{CCI}$  is the  $V_{CC}$  associated with the input port.
  - I.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.

#### Figure 6-1. Load Circuit and Voltage Waveforms

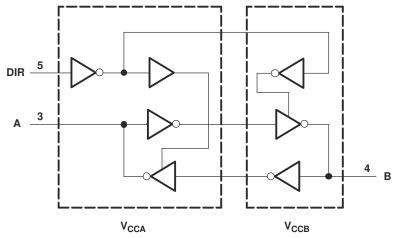


### 7 Detailed Description

#### 7.1 Overview

The SN74AVC1T45 is a single-bit, dual-supply, noninverting voltage level translation device.  $V_{CCA}$  supports pin A and the direction control pin, and  $V_{CCB}$  supports pin B. The A port can accept I/O voltages ranging from 1.08V to 3.6V, while the B port can accept I/O voltages from 1.08V to 3.6V. The high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A.

#### 7.2 Functional Block Diagram



#### 7.3 Feature Description

#### 7.3.1 Fully Configurable

The fully configurable dual-rail design allows each port to operate over the full 1.08V to 3.6V power-supply range. Both  $V_{CCA}$  and  $V_{CCB}$  can be supplied at any voltage between 1.08V and 3.6V making the device an excellent choice for translating between any of the voltage nodes (1.2V, 1.8V, 2.5V, and 3.3V).

#### 7.3.2 Support High-Speed Translation

SN74AVC1T45 can support high data-rate application. The translated signal data rate can be up to 500Mbps when signal is translated from 1.08V to 3.3V.

#### 7.3.3 Ioff Supports Partial-Power-Down Mode Operation

I<sub>off</sub> will prevent backflow current by disabling I/O output circuits when device is in partial-power-down mode.

#### 7.4 Device Functional Modes

INPUT DIR <sup>(1)</sup>	OPERATION								
L	B data to A bus								
н	A data to B bus								

#### Table 7-1. Function Table

(1) Input circuits of the data I/Os always are active.



### 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 8.1 Application Information

The SN74AVC1T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 500Mbps when device translate signal from 1.08V to 3.3V.

#### 8.1.1 Enable Times

Calculate the enable times for the SN74AVC1T45 using the following formulas:

- $t_{PZH}$  (DIR to A) =  $t_{PLZ}$  (DIR to B) +  $t_{PLH}$  (B to A)
- $t_{PZL}$  (DIR to A) =  $t_{PHZ}$  (DIR to B) +  $t_{PHL}$  (B to A)
- $t_{PZH}$  (DIR to B) =  $t_{PLZ}$  (DIR to A) +  $t_{PLH}$  (A to B)
- $t_{PZL}$  (DIR to B) =  $t_{PHZ}$  (DIR to A) +  $t_{PHL}$  (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74AVC1T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

#### **8.2 Typical Applications**

#### 8.2.1 Unidirectional Logic Level-Shifting Application

Figure 8-1 shows an example of the SN74AVC1T45 being used in a unidirectional logic level-shifting application.

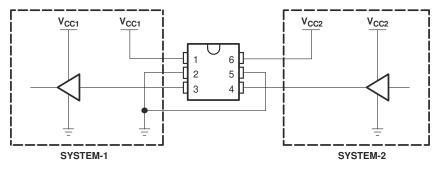


Figure 8-1. Unidirectional Logic Level-Shifting Application

PIN	NAME	FUNCTION	DESCRIPTION
1	V <sub>CCA</sub>	V <sub>CC1</sub>	SYSTEM-1 supply voltage (1.2V to 3.6V)
2	GND	GND	Device GND
3	A	OUT	Output level depends on $V_{CC1}$ voltage.
4	В	IN	Input threshold value depends on $V_{CC2}$ voltage.
5	DIR	DIR	GND (low level) determines B-port to A-port direction.
6	V <sub>CCB</sub>	V <sub>CC2</sub>	SYSTEM-2 supply voltage (1.2V to 3.6V)



#### 8.2.1.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

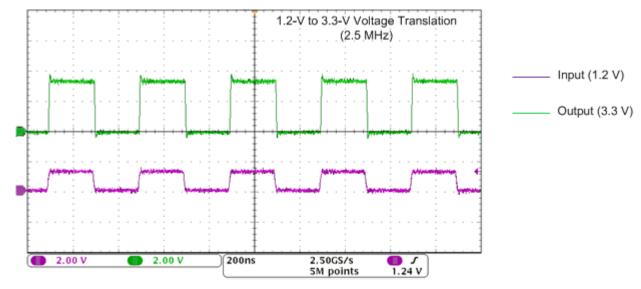
Table 8-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.2V to 3.6V
Output voltage range	1.2V to 3.6V

#### 8.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN74AVC1T45 device to determine the input voltage range. For a valid logic-high, the value must exceed the VIH of the input port. For a valid logic low the value must be less than the VIL of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN74AVC1T45 device is driving to determine the output voltage range.



8.2.1.3 Application Curve

Figure 8-2. Translation Up (1.2V to 3.3V) at 2.5MHz



#### 8.2.2 Bidirectional Logic Level-Shifting Application

Figure 8-3 shows the SN74AVC1T45 being used in a bidirectional logic level-shifting application. Because the SN74AVC1T45 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

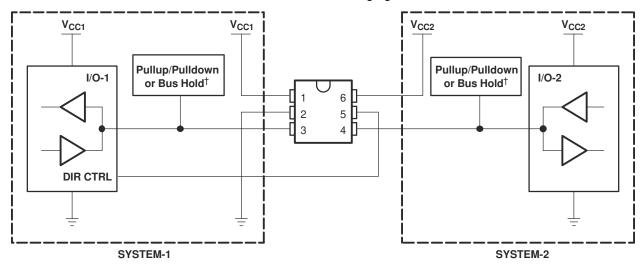


Figure 8-3. Bidirectional Logic Level-Shifting Application

The following table provides data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION								
1	Н	Out	In	SYSTEM-1 data to SYSTEM-2								
2	Н	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown. <sup>(1)</sup>								
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown. <sup>(1)</sup>								
4	L	In	Out	SYSTEM-2 data to SYSTEM-1								

Table 8-2. Data Transmission: SYSTEM-1 and SYSTEM-2

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions (for example, both pullup or both pulldown).

#### 8.2.2.1 Design Requirements

Refer to Section 8.2.1.1.

#### 8.2.2.2 Detailed Design Procedure

Refer to Section 8.2.1.2.



#### 8.2.2.3 Application Curve

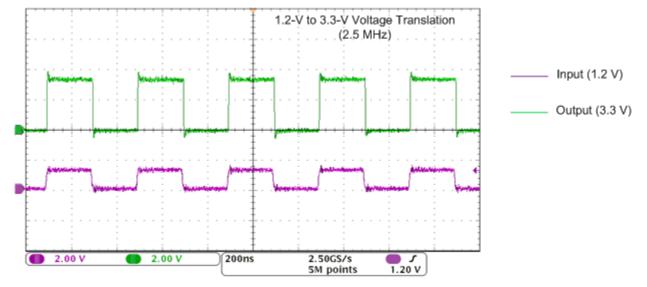


Figure 8-4. Translation Up (1.2V to 3.3V) at 2.5MHz

#### 8.3 Power Supply Recommendations

The SN74AVC1T45 device uses two separate configurable power-supply rails,  $V_{CCA}$  and  $V_{CCB}$ .  $V_{CCA}$  accepts any supply voltage from 1.08V to 3.6V, and  $V_{CCB}$  accepts any supply voltage from 1.08V to 3.6V. The A port and B port are designed to track  $V_{CCA}$  and  $V_{CCB}$  respectively allowing for low-voltage, bidirectional translation between any of the 1.2V, 1.5 -V, 1.8V, and 3.3V voltage nodes.

#### 8.3.1 Power-Up Considerations

A proper power-up sequence always should be followed to avoid excessive supply current, bus contention, oscillations, or other anomalies. To guard against such power-up problems, take the following precautions:

- 1. Connect ground before any supply voltage is applied.
- 2. Power up V<sub>CCA</sub>.
- 3. V<sub>CCB</sub> can be ramped up along with or after V<sub>CCA</sub>.

V		V <sub>CCA</sub>												
V <sub>CCB</sub>	0V	1.2V	1.5V	1.8V	2.5V	3.3V	UNIT							
0V	0	<0.5	<0.5	<0.5	<0.5	<0.5								
1.2V	<0.5	<1	<1	<1	<1	1								
1.5V	<0.5	<1	<1	<1	<1	1								
1.8V	<0.5	<1	<1	<1	<1	<1	μA							
2.5V	<0.5	1	<1	<1	<1	<1	1							
3.3V	<0.5	1	<1	<1	<1	<1								

#### 8.4 Layout

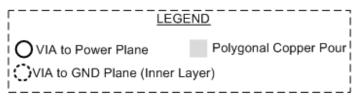
#### 8.4.1 Layout Guidelines

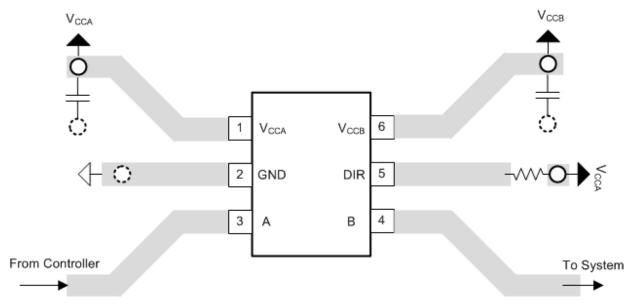
For device reliability, it is recommended to follow common printed-circuit board layout guidelines such as follows:

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.



#### 8.4.2 Layout Example









### 9 Device and Documentation Support

#### 9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 9.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 9.3 Trademarks

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#### 9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 9.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### **10 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision I (March 2024) to Revision J (August 2024)	Page
•	Updated Thermal Metrics	6

С	hanges from Revision H (October 2014) to Revision I (March 2024)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Updated the package information table to include package lead size	1

0	Changes from Revision G (January 2008) to Revision H (October 2014)	Page
•	Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Devic	е
	Functional Modes, Application and Implementation section, Power Supply Recommendations section, I	Layout
	section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Inform	nation
	section	

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AVC1T45DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(DT1F, DT1R) (DT1H, DT1P)	Samples
SN74AVC1T45DBVRE4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(DT1F, DT1R) (DT1H, DT1P)	Samples
SN74AVC1T45DBVRG4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(DT1F, DT1R) (DT1H, DT1P)	Samples
SN74AVC1T45DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	Call TI   NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT1R DT1H	Samples
SN74AVC1T45DBVTE4	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT1R DT1H	Samples
SN74AVC1T45DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(TCF, TCR) (TCH, TCP)	Samples
SN74AVC1T45DCKRE4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TCF, TCR) (TCH, TCP)	Samples
SN74AVC1T45DCKRG4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TCF, TCR) (TCH, TCP)	Samples
SN74AVC1T45DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TCF, TCR) (TCH, TCP)	Samples
SN74AVC1T45DCKTG4	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TCF, TCR) (TCH, TCP)	Samples
SN74AVC1T45DRLR	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(1JW, TCR) TCH	Samples
SN74AVC1T45DRLRG4	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(1JW, TCR) TCH	Samples
SN74AVC1T45YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(TC2, TCN)	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



#### www.ti.com

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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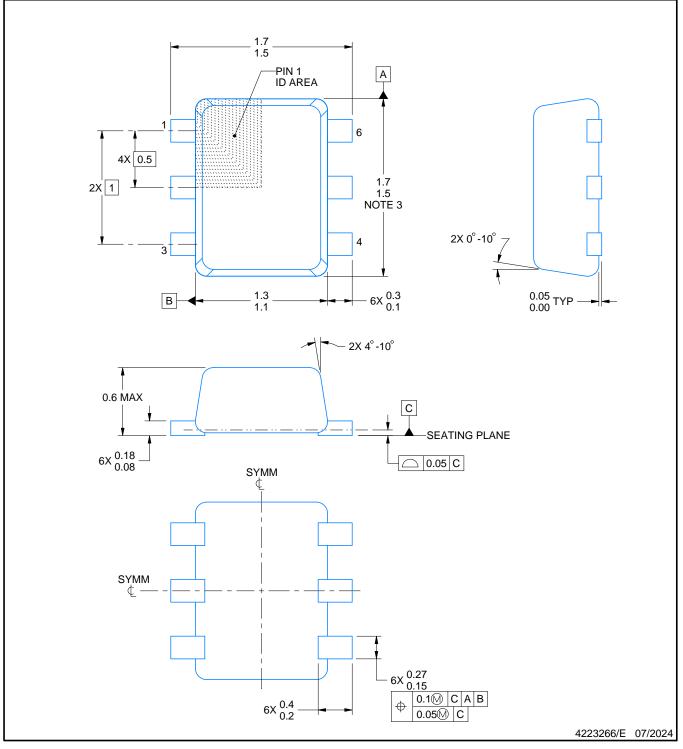
# **DRL0006A**



# **PACKAGE OUTLINE**

## SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-293 Variation UAAD

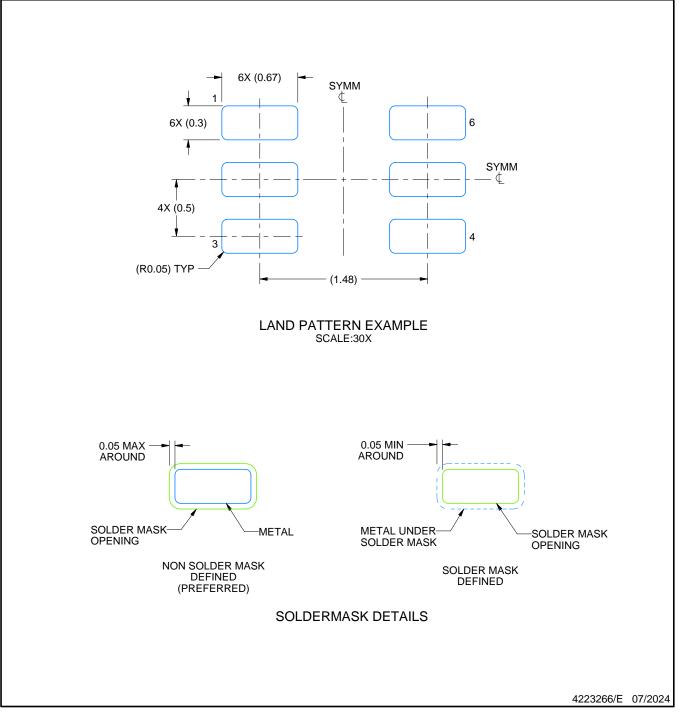


## **DRL0006A**

# **EXAMPLE BOARD LAYOUT**

### SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
 7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.

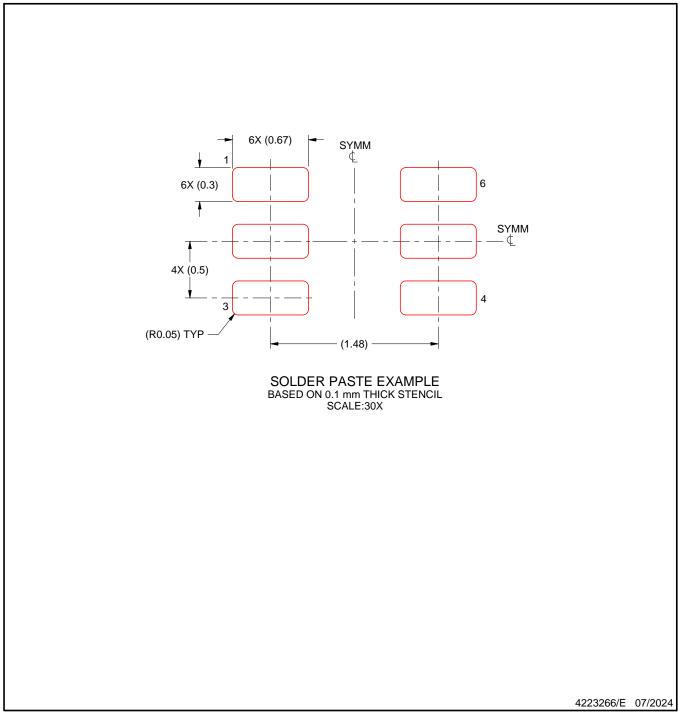


## **DRL0006A**

# **EXAMPLE STENCIL DESIGN**

### SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



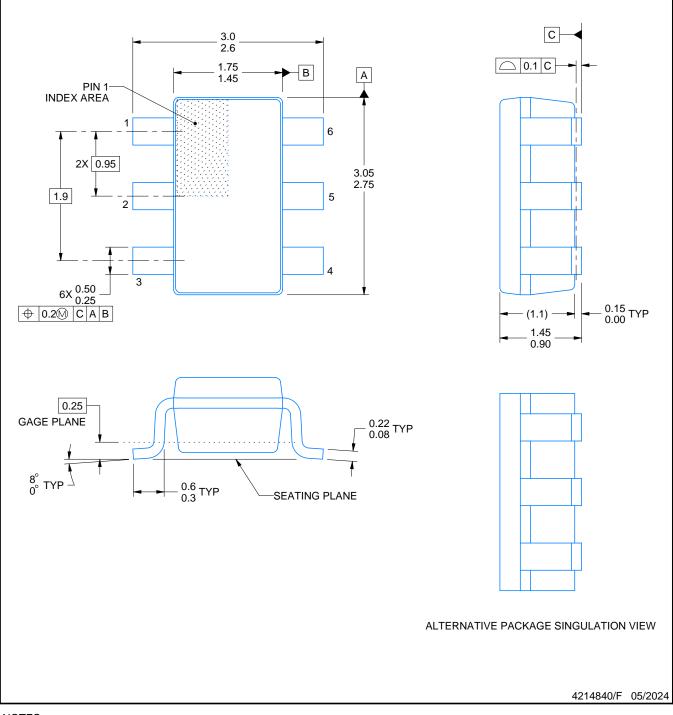
# **DBV0006A**



## **PACKAGE OUTLINE**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.

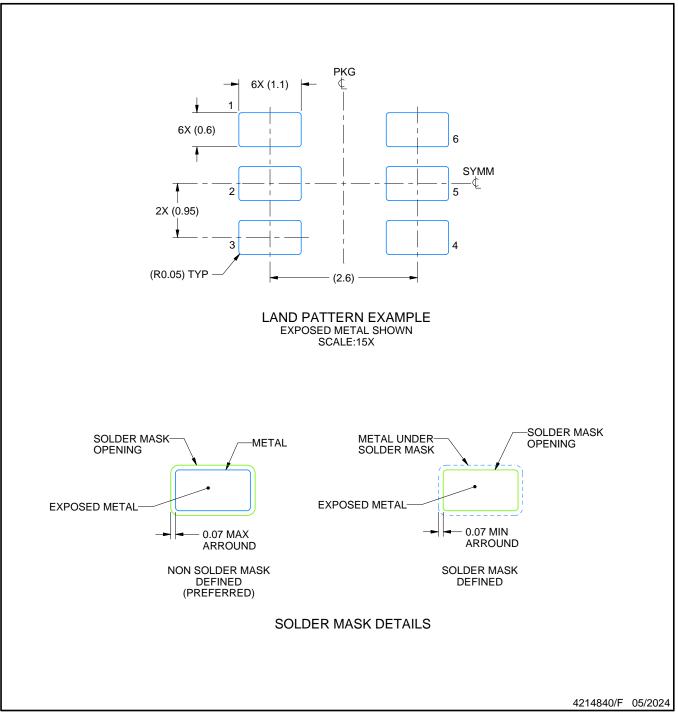


## **DBV0006A**

# **EXAMPLE BOARD LAYOUT**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

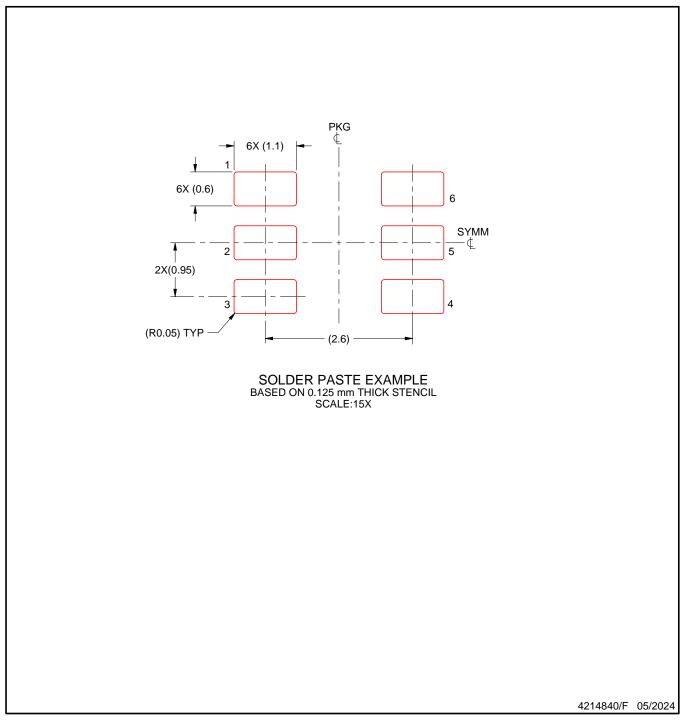


## **DBV0006A**

# **EXAMPLE STENCIL DESIGN**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



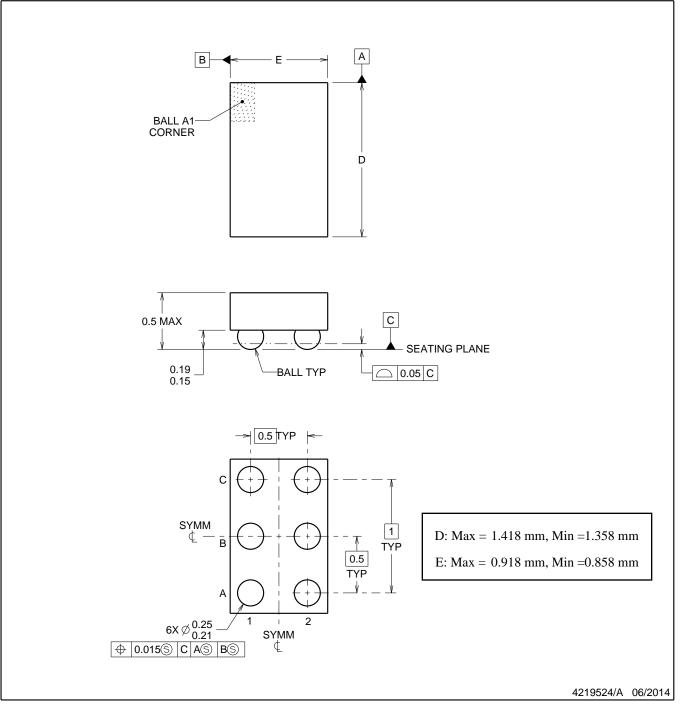
# **YZP0006**



# **PACKAGE OUTLINE**

## DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. NanoFree<sup>™</sup> package configuration.

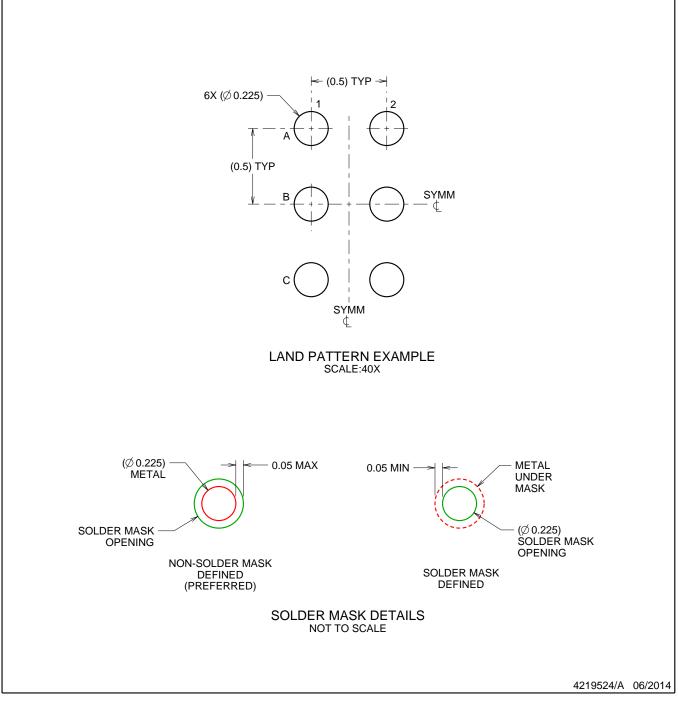


# YZP0006

# **EXAMPLE BOARD LAYOUT**

### DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).

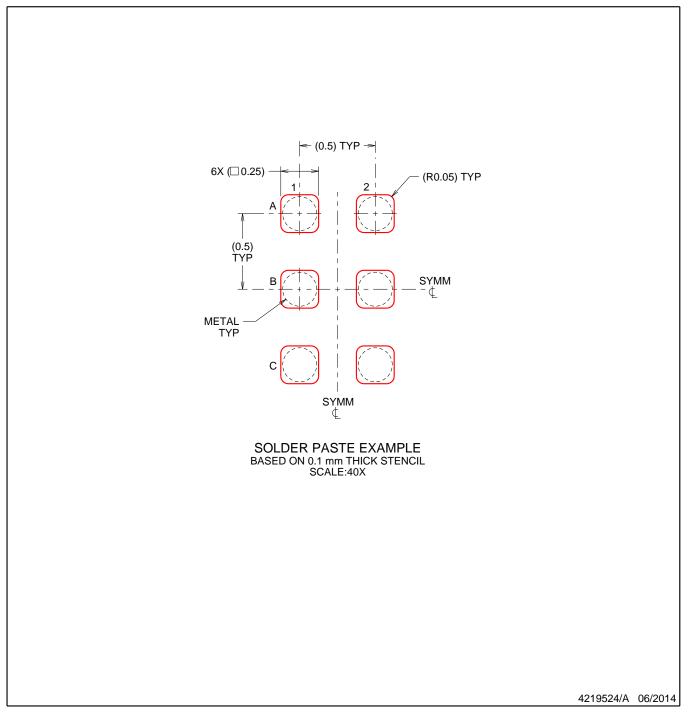


# YZP0006

# **EXAMPLE STENCIL DESIGN**

### DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



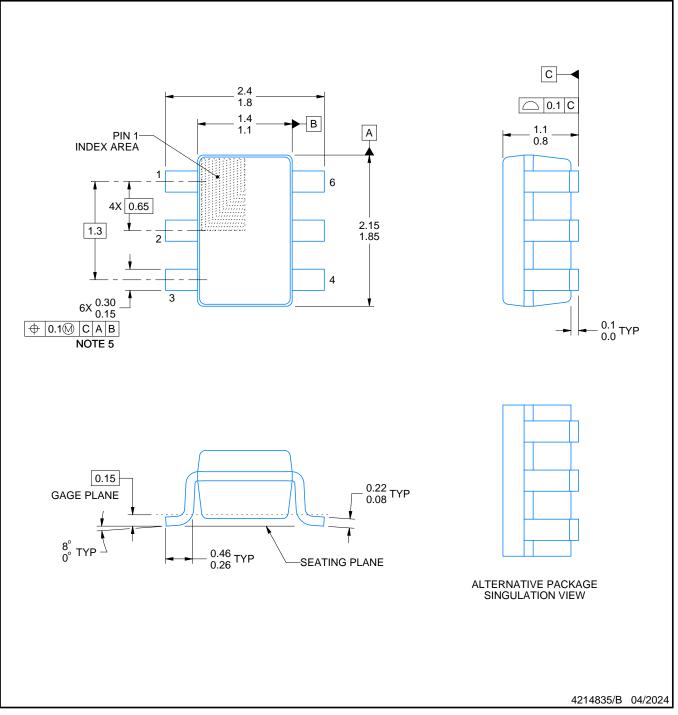
# **DCK0006A**



# **PACKAGE OUTLINE**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.
   Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
   Falls within JEDEC MO-203 variation AB.

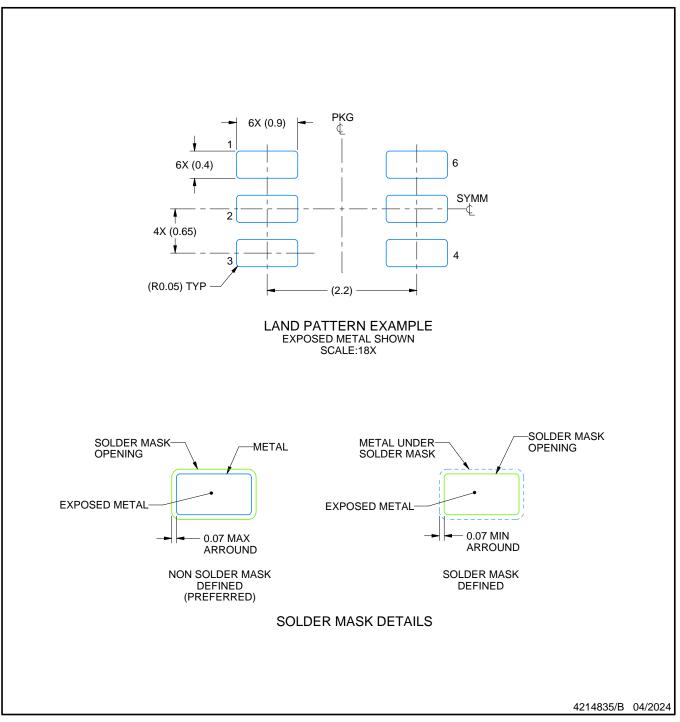


## **DCK0006A**

# **EXAMPLE BOARD LAYOUT**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

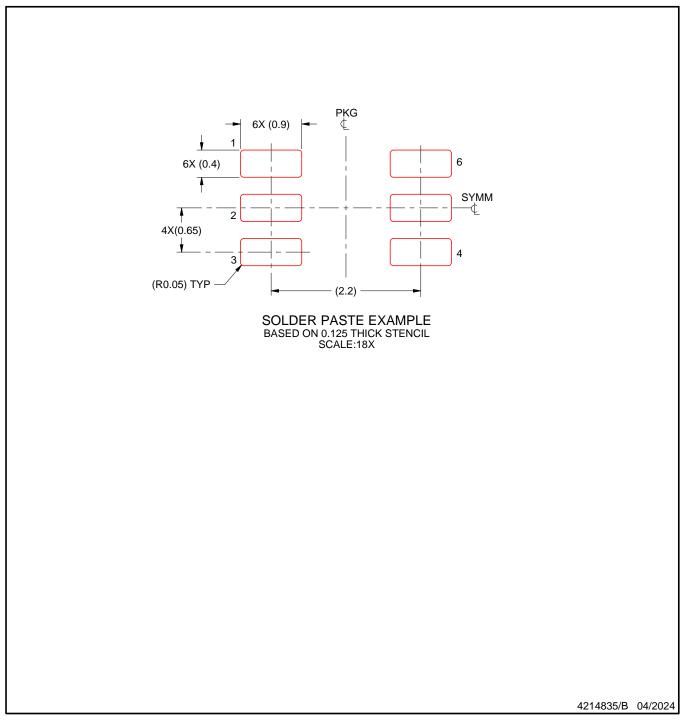


## **DCK0006A**

# **EXAMPLE STENCIL DESIGN**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



<sup>7.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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